

IN THE CLAIMS:

1. (Currently amended) An electron beam aligner comprising:

a substrate holder provided within [[a]] an exposure chamber, and for holding a [[semiconductor]] substrate on [[a]] which surface [[of which]] a resist film is formed;

electron beam irradiation means for [[fully]] irradiating said resist film with an electron beam; and

gas collection means provided on said exposure chamber by directly connecting thereto, and for collecting an outgassing released from said resist film when irradiated with said electron beam.

2. (Original) The electron beam aligner of Claim 1, further comprising gas analysis means for analyzing a constituent of said outgassing collected by said gas collection means.

3. (Currently amended) An electron beam aligner comprising:

a substrate holder provided within [[a]] an exposure chamber, and for holding a [[semiconductor]] substrate on [[a]] which surface [[of which]] a resist film is formed;

electron beam irradiation means for [[fully]] irradiating said resist film with an electron beam; and

gas analysis means provided on said exposure chamber by directly connecting thereto, and for analyzing a constituent of an outgassing released from said resist film when irradiated with said electron beam.

4. (Currently amended) An outgassing collection method comprising the steps of:

holding, within [[a]] an exposure chamber, a [[semiconductor]] substrate on [[a]] which surface [[of which]] a resist film is formed;

[[fully]] irradiating said resist film with an electron beam; and

collecting an outgassing released from said resist film when irradiated with said electron beam.

5. (Currently amended) An outgassing analysis method comprising the steps of:

holding, within [[a]] an exposure chamber, a [[semiconductor]] substrate on [[a]] which surface [[of which]] a resist film is formed;

[[fully]] irradiating said resist film with an electron beam;

collecting an outgassing released from said resist film when irradiated with said electron beam; and

analyzing a constituent of said collected outgassing.

6. (Currently amended) An outgassing analysis method comprising the steps of:

holding, within [[a]] an exposure chamber, a [[semiconductor]] substrate on [[a]] which surface [[of which]] a resist film is formed;

[[fully]] irradiating said resist film with an electron beam; and

analyzing a constituent of an outgassing released from said resist film when irradiated with said electron beam.
